

CoolMOS™ Power Transistor
Features

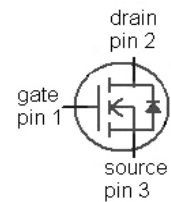
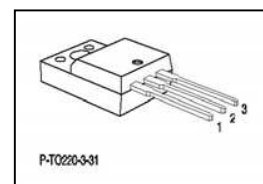
- Lowest figure of merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Pb-free lead plating; RoHS compliant; Halogen free for mold compound
- Qualified for industrial grade applications according to JEDEC⁰⁾

Product Summary

| | | |
|---------------------|-------|----------|
| $V_{DS} @ T_{jmax}$ | 550 | V |
| $R_{DS(on),max}$ | 0.350 | Ω |
| $Q_{g,typ}$ | 19 | nC |

CoolMOS CP is designed for:

- Hard and softswitching SMPS topologies
- CCM PFC for Notebook adapter, PDP and LCD TV
- PWM for Notebook adapter, PDP and LCD TV

TO220 Full PAK


| Type | Package | Marking |
|-------------|------------|---------|
| IPA50R350CP | PG-TO220FP | 5R350P |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|-------------------|---|-------------|--------------------|
| Continuous drain current ¹⁾ | I_D | $T_C=25\text{ °C}$ | 10 | A |
| | | $T_C=100\text{ °C}$ | 6 | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | $T_C=25\text{ °C}$ | 22 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=3.7\text{ A}$, $V_{DD}=50\text{ V}$ | 246 | mJ |
| Avalanche energy, repetitive $t_{AR}^{2),3)}$ | E_{AR} | $I_D=3.7\text{ A}$, $V_{DD}=50\text{ V}$ | 0.37 | |
| Avalanche current, repetitive $t_{AR}^{2),3)}$ | I_{AR} | | 3.7 | A |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS}=0\dots400\text{ V}$ | 50 | V/ns |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f>1\text{ Hz}$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 32 | W |
| Operating and storage temperature | T_j , T_{stg} | | -55 ... 150 | $^{\circ}\text{C}$ |
| Mounting torque | | M2.5 screws | 60 | Ncm |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|---------------|--------------------|-------|------|
| Continuous diode forward current ¹⁾ | I_S | $T_C=25\text{ °C}$ | 5.6 | A |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | | 22 | |
| Reverse diode dv/dt ⁴⁾ | dv/dt | | 15 | V/ns |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|--|------------|---------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 3.9 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 62 | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | 1.6 mm (0.063 in.) from case for 10 s | - | - | 260 | °C |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|------|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$ | 500 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=0.37\text{ mA}$ | 2.5 | 3 | 3.5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=500\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$ | - | - | 1 | μA |
| | | $V_{DS}=500\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$ | - | 10 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}, I_D=5.6\text{ A}, T_j=25\text{ °C}$ | - | 0.32 | 0.35 | Ω |
| | | $V_{GS}=10\text{ V}, I_D=5.6\text{ A}, T_j=150\text{ °C}$ | - | 0.80 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}, \text{open drain}$ | - | 2.2 | - | Ω |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|---|---|------|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$ | - | 1020 | - | pF |
| Output capacitance | C_{oss} | | - | 46 | - | |
| Effective output capacitance, energy related ⁵⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 400 V | - | 43 | - | |
| Effective output capacitance, time related ⁶⁾ | $C_{o(tr)}$ | | - | 92 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=5.6\text{ A},$ $R_G=30.9\ \Omega$ | - | 35 | - | ns |
| Rise time | t_r | | - | 14 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 80 | - | |
| Fall time | t_f | | - | 12.0 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=400\text{ V}, I_D=5.6\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 4 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 6 | - | |
| Gate charge total | Q_g | | - | 19 | 25 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 5.2 | - | V |

Reverse Diode

| | | | | | | |
|-------------------------------|-----------|--|---|-----|-----|---------------|
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=5.6\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 0.9 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 250 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 2.3 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 19 | - | A |

⁰⁾ J-STD20 and JESD22

¹⁾ Limited only by $T_{j,max}$
²⁾ Pulse width t_p limited by $T_{j,max}$
³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

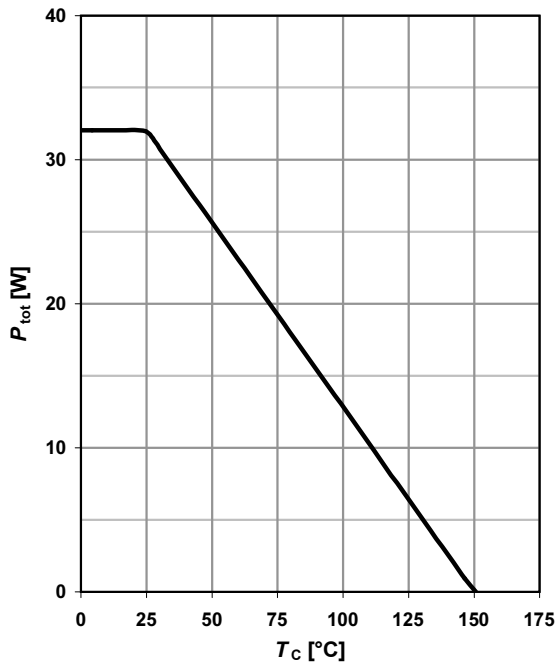
⁴⁾ $I_{SD} \leq I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

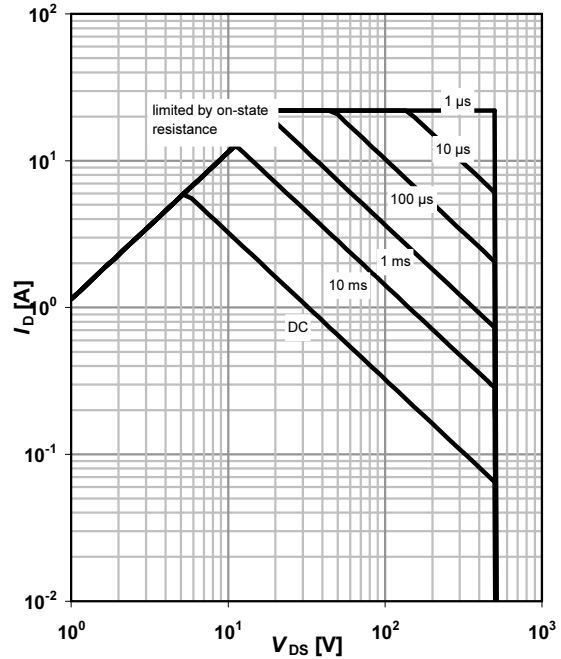
$P_{tot}=f(T_c)$



2 Safe operating area

$I_D=f(V_{DS}); T_c=25\text{ }^\circ\text{C}; D=0$

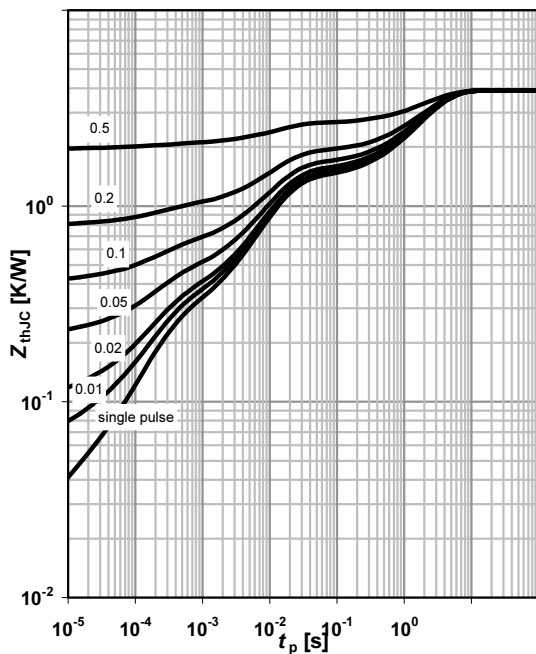
parameter: t_p



3 Max. transient thermal impedance

$Z_{(th)C}=f(t_p)$

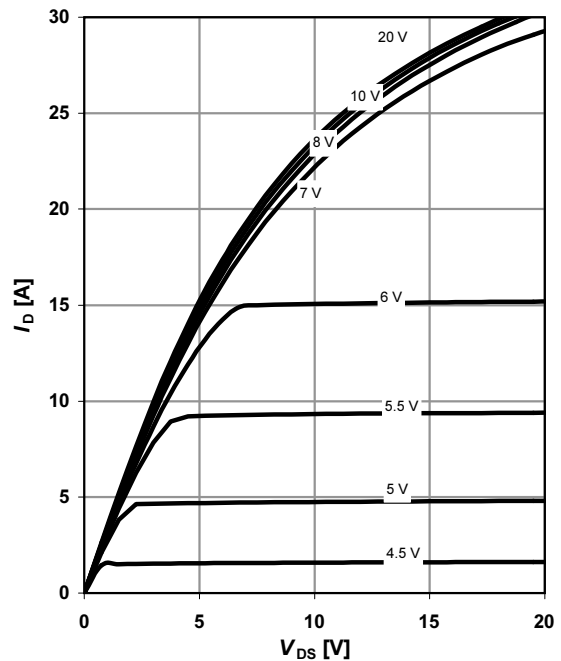
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

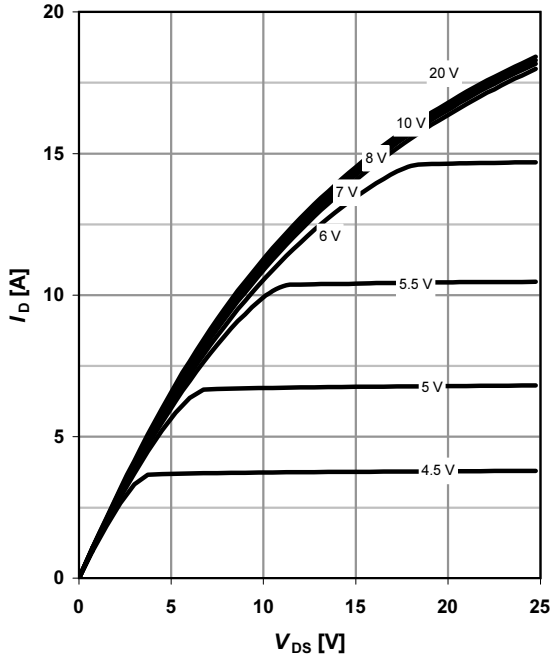
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

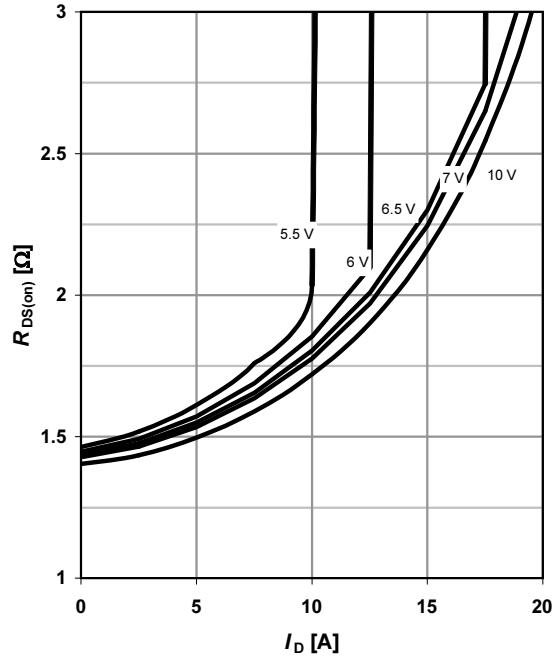
parameter: V_{GS}



6 Typ. drain-source on-state resistance

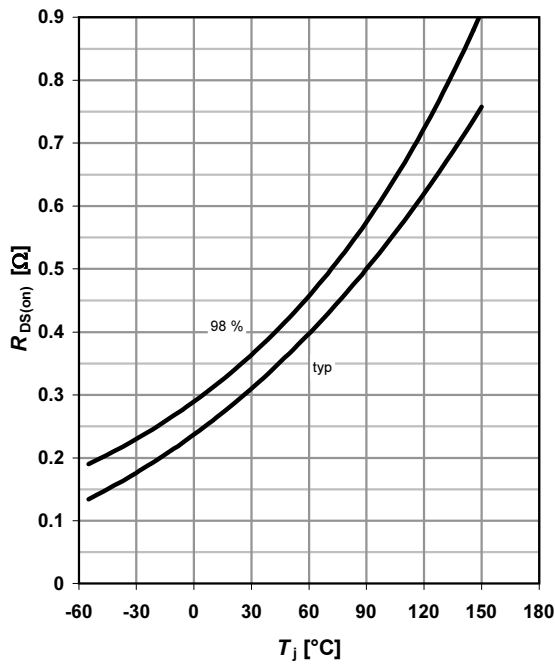
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

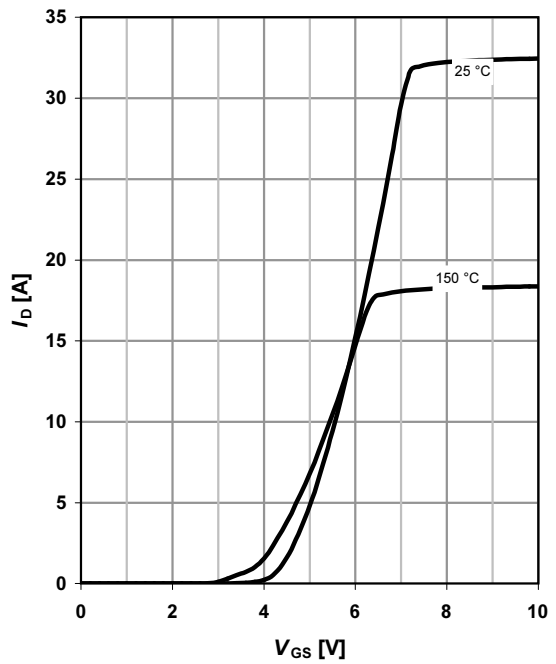
$R_{DS(on)} = f(T_j); I_D = 5.6\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

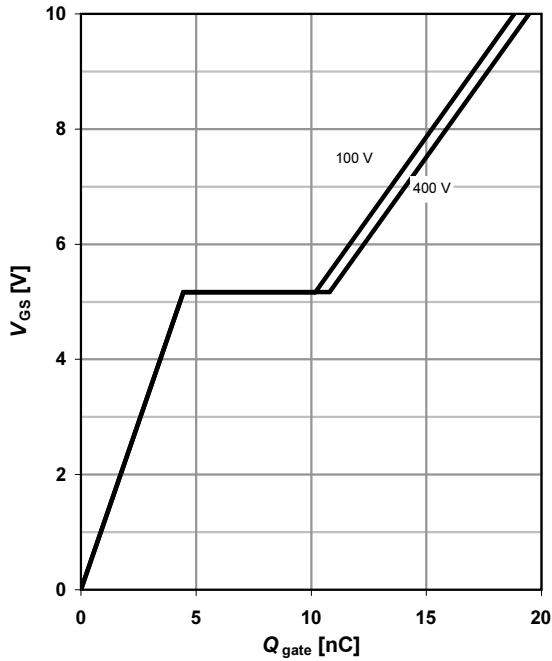
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=5.6$ A pulsed

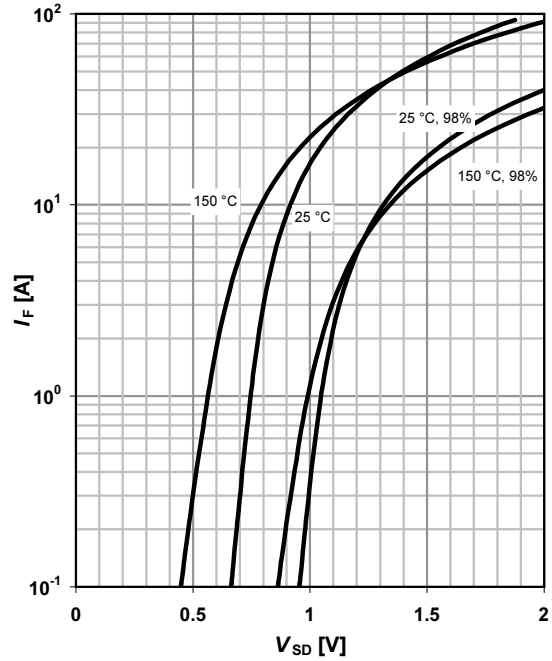
parameter: V_{DD}



10 Forward characteristics of reverse diode

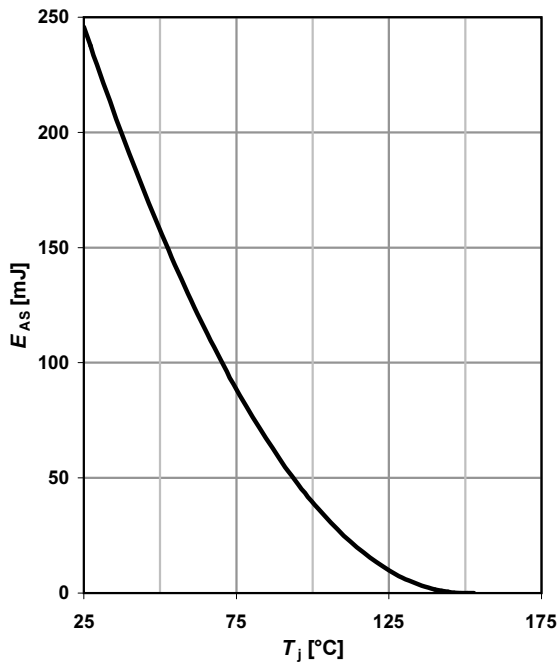
$I_F=f(V_{SD})$

parameter: T_j



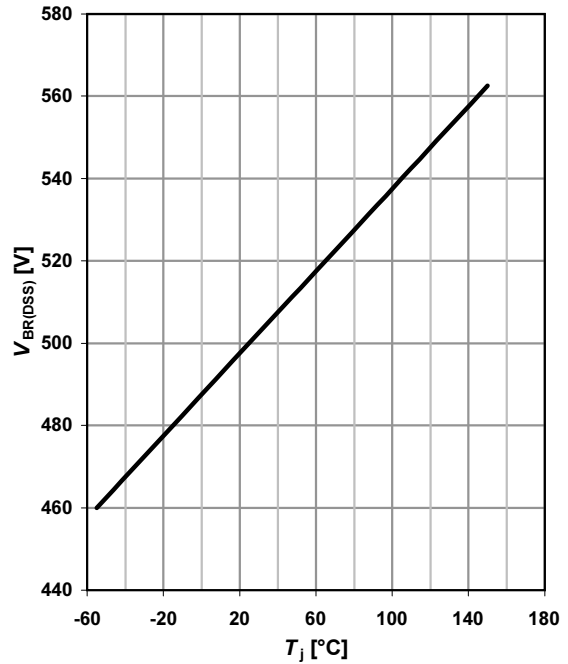
11 Avalanche energy

$E_{AS}=f(T_j); I_D=3.7$ A; $V_{DD}=50$ V



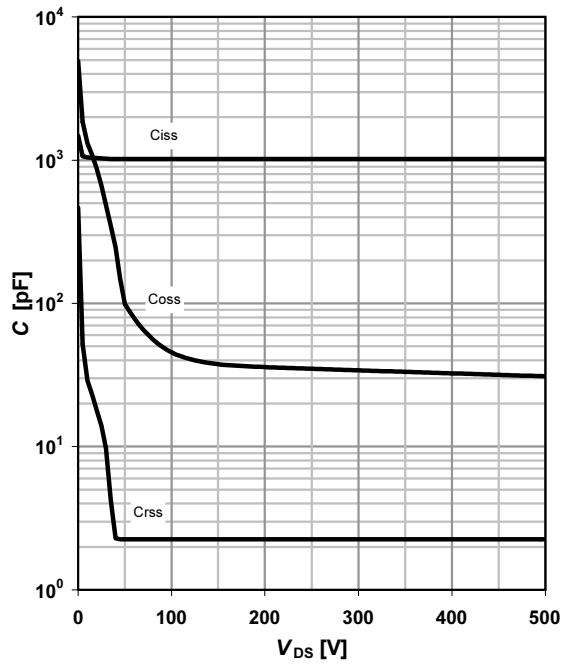
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25$ mA



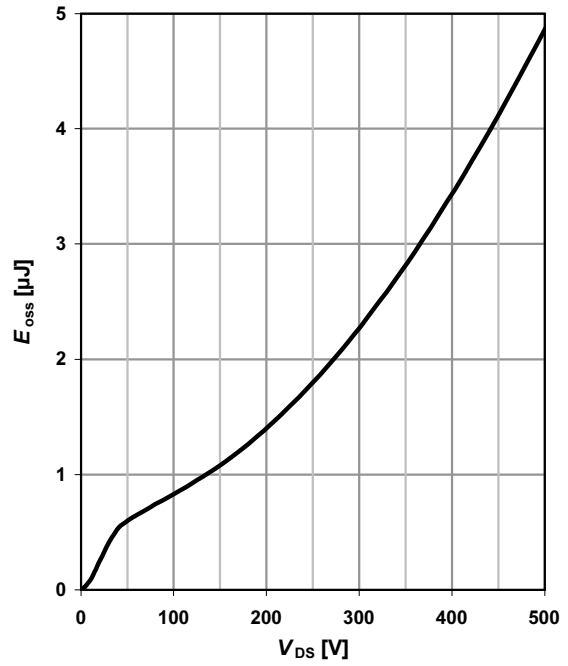
13 Typ. capacitances

$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

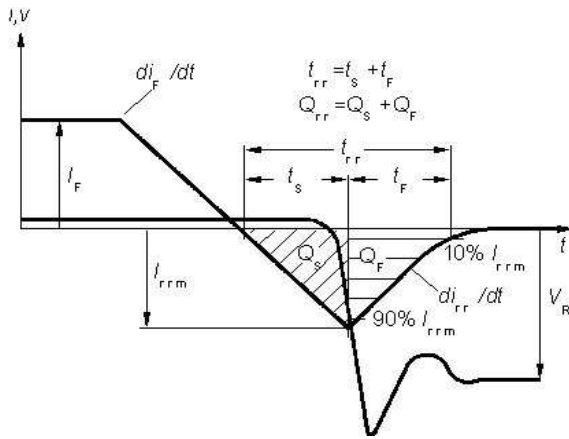


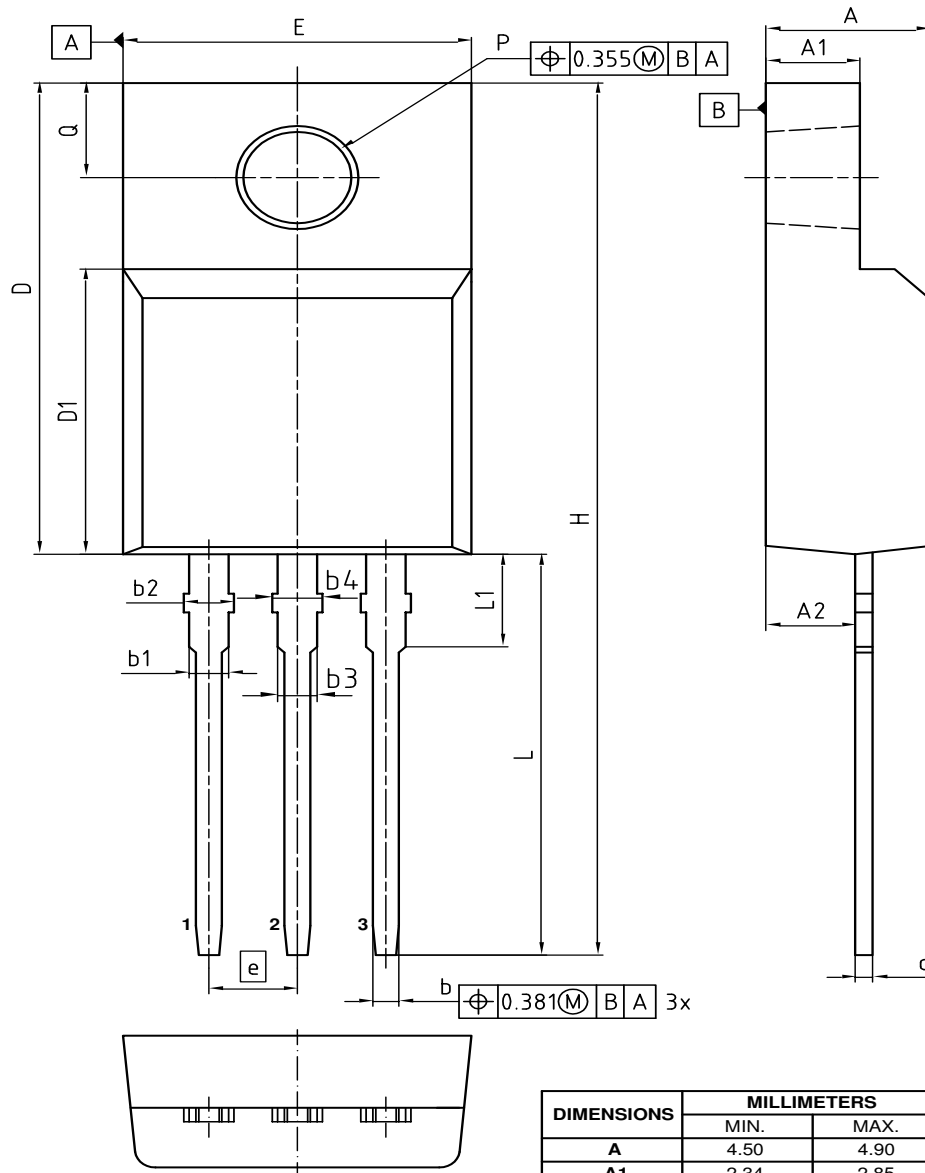
14 Typ. Coss stored energy

$$E_{oss} = f(V_{DS})$$



Definition of diode switching characteristics



Outline PG-TO220 FullPAK


NOTES:
 ALL DIMENSIONS REFER TO JEDEC STANDARD TO-281
 AND DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS
 OR GATE BURRS
 GATE BURRS ARE LESS THAN 0.5 mm

| DIMENSIONS | MILLIMETERS | |
|------------|-------------|-------|
| | MIN. | MAX. |
| A | 4.50 | 4.90 |
| A1 | 2.34 | 2.85 |
| A2 | 2.42 | 2.86 |
| b | 0.65 | 0.90 |
| b1 | 0.95 | 1.38 |
| b2 | 0.95 | 1.51 |
| b3 | 0.65 | 1.38 |
| b4 | 0.65 | 1.51 |
| c | 0.40 | 0.63 |
| D | 15.67 | 16.15 |
| D1 | 8.97 | 9.83 |
| E | 10.00 | 10.65 |
| e | 2.54 | |
| H | 28.70 | 29.75 |
| L | 12.78 | 13.75 |
| L1 | 2.83 | 3.45 |
| øP | 3.00 | 3.30 |
| Q | 3.15 | 3.50 |

| |
|------------------------------------|
| DOCUMENT NO. Z8B00003319 |
| REVISION 07 |
| SCALE 5:1 0 1 2 3 4 5mm |
| EUROPEAN PROJECTION |
| ISSUE DATE 27.01.2017 |

500V CoolMOS™ CP Power Transistor

IPA50R350CP

Revision History

IPA50R350CP

Revision: 2018-02-26, Rev. 2.2

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.2 | 2018-02-26 | Outline PG-TO220 FullPAK update |

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Published by

Infineon Technologies AG

81726 München, Germany

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